# Switching (250V, 12A)

# **RDN120N25**

#### Features

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) Exellent resistance to damage from static electricity.

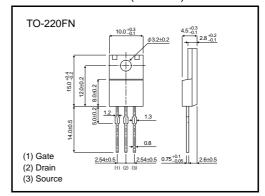
## Application

Switching

#### Structure

Silicon N-channel MOS FET

# ●External dimensions (Unit: mm)

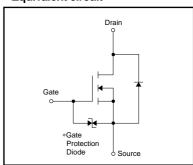


### ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		VDSS	250	V
Gate-Source Voltage		$V_{GSS}$	±30	V
Drain Current	Continuous	lσ	12	Α
	Pulsed	I <sub>DP</sub> *1	48	Α
Reverse Drain Current	Continuous	I <sub>DR</sub>	12	Α
	Pulsed	I <sub>DRP</sub> *1	48	Α
Avalanche Current		I <sub>AS</sub> *2	12	Α
Avalanche Energy		Eas *2	216	mJ
Total Power Dissipation (Tc=25°C)		$P_D$	40	W
Channel Temperature		T <sub>ch</sub>	150	°C
Storage Temperature		T <sub>stg</sub>	-55 to +150	°C

- \*1 Pw  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1% \*2 L  $\rightleftharpoons$  2.4mH, V<sub>DD</sub>=50V, Rg=25 $\Omega$ , 1Pulse, Tch=25°C

#### ●Equivalent circuit



\*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-Source Leakage	lgss	_	_	±10	μА	Vgs=±30V, Vps=0V
Drain-Source Breakdown Voltage	V(BR) DSS	250	_	_	V	I <sub>D</sub> =250μA, V <sub>G</sub> s=0V
Zero Gate Voltage Drain Current	Ipss	_	_	25	μΑ	Vps=250V, Vgs=0V
Gate Threshold Voltage	VGS (th)	2.0	_	4.0	V	VDS=10V, ID=1mA
Static Drain-Source On-State Resistance	RDS (on)	_	0.16	0.21	Ω	Ib=6A, Vgs=10V
Forward Transfer Admittance	Yfs	3.7	6.1	_	S	Vps=10V, Ip=6.0A
Input Capacitance	Ciss	_	1224	_	pF	V <sub>DS</sub> =10V
Output Capacitance	Coss	_	443	_	pF	V <sub>GS</sub> =0V
Reverse Transfer Capacitance	Crss	_	154	_	pF	f=1MHz
Turn-On Delay Time	td (on)	_	17	_	ns	ID=6.0A, VDD≒100V
Rise Time	tr	_	32	_	ns	Vgs=10V
Turn-Off Delay Time	td (off)	_	58	_	ns	R <sub>L</sub> =16.7Ω
Fall Time	<b>t</b> f	_	28	_	ns	Rgs=10Ω
Reverse Recovery Time	trr	_	169	_	ns	IDR=12A, VGS=0V
Reverse Recovery Charge	Qrr	_	0.95	_	μС	di/dt=100A / μs
Total Gate Charge	Qg	_	31	_	nC	VDD=125V,VGS=10V,ID=12A

# •Electrical characteristic curves

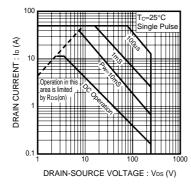


Fig.1 Maximun Safe Operating Area

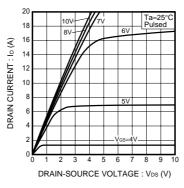


Fig.2 Typical Output Characteristics

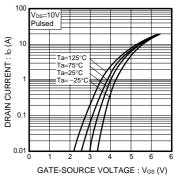


Fig.3 Typical Transfer Characteristics

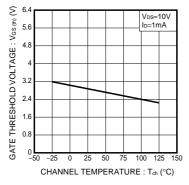


Fig.4 Gate Threshold Voltage vs. Channel Temperature

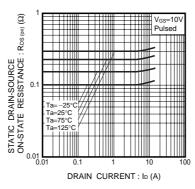


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

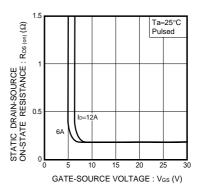


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

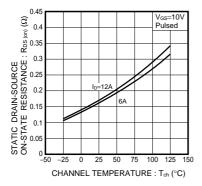


Fig.7 Static Drain-Source On-State Resistance vs. Channel Temperature

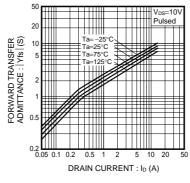


Fig.8 Forward Transfer Admittance vs. Drain Current

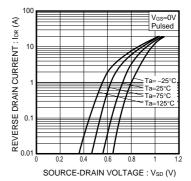


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

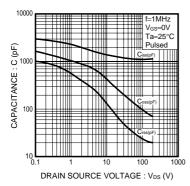


Fig.10 Typical Capacitance vs. Drain-Source Voltage

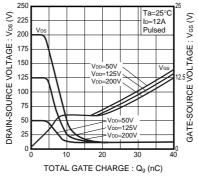


Fig.11 Dynamic Input Characteristics

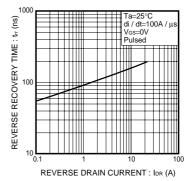


Fig.12 Reverse Recovery Time vs. Reverse Drain Current

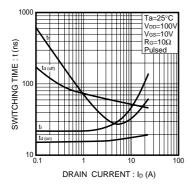


Fig.13 Switching Characteristcs

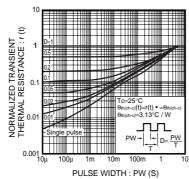


Fig.14 Normalized Transient Thermal Resistance vs. Pulse Width

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